Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (resist$3 adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L2	20	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (transistor near3 resistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L3	34	((single near3 event near3 upset) SEU) and ((var$5 program$5 adjust$4) near3 (impedance resistance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L4	67	(((single near3 event near3 upset) SEU)) and ohm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L5	54	((single near3 event near3 upset) or SEU) and ((resist$4 imped$5) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L6	30	((control$5 program$5 adjust$4 variable) with transistor with (resist$4 imped$4)) and ((single near3 event near3 upset) or SEU)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:58
L7	14	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and ((resist$3 imped$3) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L8	3	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (program$5 near4 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L9	0	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (program$5 near4 (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59

L10	2	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (program$5 with transistor with (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L11	3	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (program$5 near4 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L12	0	((((((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))) and memory) and (sram)) and (program$5 near4 (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L13	65	((((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L14	42	((((((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))) and memory) and (sram)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L15	85	(((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 15:59
L16	22	US-4956814-$.DID. OR US-5126279-$.DID. OR US-5301146-$.DID. OR US-5307142-$.DID. OR US-5311070-$.DID. OR US-5889431-$.DID. OR US-6058041-$.DID. OR US-6172907-$.DID. OR US-6180984-$.DID. OR US-6271568-$.DID. OR US-6278287-$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:09
L17	24	US-4725875-$.DID. OR US-4852060-$.DID. OR US-4884238-$.DID. OR US-4903094-$.DID. OR US-5018102-$.DID. OR US-5189598-$.DID. OR US-5212108-$.DID. OR US-5631863-$.DID. OR US-6111780-$.DID. OR US-6252433-$.DID. OR US-6278287-$.DID. OR US-6369630-$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:09

L18	44	L16 or L17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:09
L19	23	(US-20020109230-$).did. or (US-4725875-$ or US-4884238-$ or US-4903094-$ or US-4956814-$ or US-5018102-$ or US-5126279-$ or US-5189598-$ or US-5212108-$ or US-5301146-$ or US-5307142-$ or US-5311070-$ or US-5631863-$ or US-5889431-$ or US-6058041-$ or US-6111780-$ or US-6172907-$ or US-6180984-$ or US-6252433-$ or US-6271568-$ or US-6369630-$).did. or (DE-3871945-$ or US-6278287-$). did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/02/07 16:09
L20	1	L19 not L18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 16:10
S1	25	((control$5 program$5 adjust$4 variable) with transistor with (resist$4 imped$4)) and ((single near3 event near3 upset) or SEU)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S2	51	((single near3 event near3 upset) or SEU) and ((resist$4 imped$5) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S3	61	(((single near3 event near3 upset) SEU)) and ohm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S4	30	((single near3 event near3 upset) SEU) and ((var$5 program$5 adjust$4) near3 (impedance resistance))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S5	19	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (transistor near3 resistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34

S6	6	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (resist$3 adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/15 20:34
S7	70	(((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:01
S8	53	((((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 18:51
S9	33	(((((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))) and memory) and (sram)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 18:52
S10	0	((((((single near3 event near3 upset) SEU) near3 (resist$3 imped$3))) and memory) and (sram)) and (program$5 near4 (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 18:52
S11	73	(((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:48
S12	12	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and ((resist$3 imped$3) near2 value)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:06
S13	0	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (program$5 with transistor with (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:08
S14	0	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (program$5 near4 (resist$3 imped$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:08
S15	0	((((single near3 event near3 upset) SEU) near5 (resist$3 imped$3))) and (program$5 near4 transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:35

S16	48814	resist$3 near2 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:35
S17	76238	transistor near3 resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/07/31 19:50
S18	59077	(control$5 program$5 adjust$4 variable) with transistor with (resist$4 imped$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:48
S19	18885	(control$5 program$5 adjust$4 variable) near4 transistor near4 (resist$4 imped$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:48
S20	838	(single near3 event near3 upset) or SEU	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/01 18:49
S21	841	((single near3 event near3 upset) SEU)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/18 18:11
S22	143	(((single near3 event near3 upset) SEU)) and memory and (resist$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/18 14:03
S23	21	(US-6369630-$ or US-6271568-$ or US-6180984-$ or US-6058041-$ or US-5311070-$ or US-5307142-$ or US-5212108-$ or US-5189598-$ or US-4956814-$ or US-6252433-$ or US-6172907-$ or US-5889431-$ or US-5301146-$ or US-5018102-$ or US-4884238-$ or US-6111780-$ or US-5631863-$ or US-4903094-$).did. or (US-20020109230-$).did. or (US-6278287-$ or DE-3871945-$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2003/08/18 15:36

S24	7	((US-6369630-$ or US-6271568-$ or US-6180984-$ or US-6058041-$ or US-5311070-$ or US-5307142-$ or US-5212108-$ or US-5189598-$ or US-4956814-$ or US-6252433-$ or US-6172907-$ or US-5889431-$ or US-5301146-$ or US-5018102-$ or US-4884238-$ or US-6111780-$ or US-5631863-$ or US-4903094-$).did. or (US-20020109230-$).did. or (US-6278287-$ or DE-3871945-$).did.) and ohm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/08/18 15:40
S25	0	10/125,666	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/17 19:51
S26	6400	resist$3 adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/05/20 17:39
S27	1	10/125,666	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 13:43